

16. The monitoring semiconductor substrate of claim 14, wherein the specific distance of each set of scribe marks from the periphery of said silicon substrate is between about 0.75 to 1.25 mm.

17. The monitoring semiconductor substrate of claim 14, wherein the depth of each individual scribe mark, in said silicon substrate, is between about 2.0 to 3.0 μm .

18. The monitoring semiconductor substrate of claim 14, wherein the specific width of each individual scribe mark is about 0.11 mm.

19. The monitoring semiconductor substrate of claim 14, wherein the specific length of each individual scribe mark, including the adjacent number mark, is between about 3.75 to 4.25 mm.

20. The monitoring semiconductor substrate of claim 14, wherein the specific space between individual scribe marks is between about 0.75 to 1.25 mm.

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